

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

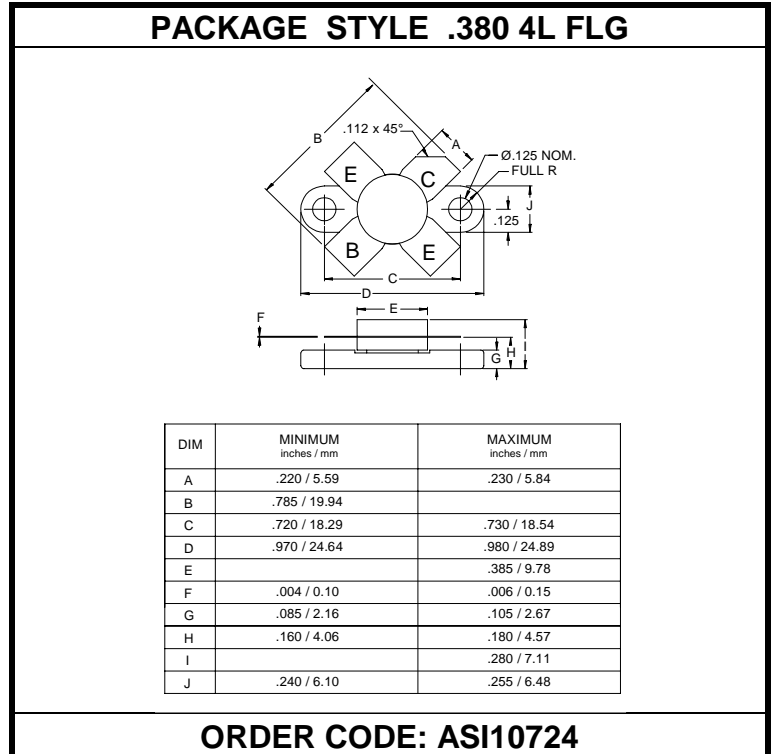
The **ASI VHB25-28F** is an NPN power transistor, designed for 108-175 MHz applications. The device utilizes diffused emitter resistor to achieve good VSWR capability.

**FEATURES:**

- Common Emitter – Class-C
- $P_G = 10$  dB at 30 W/150 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	4.0 A
$V_{CBO}$	65 V
$V_{EBO}$	4.0 V
$V_{CEO}$	35 V
$P_{DISS}$	40 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	4.4 °C/W


**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 200$ mA			35			V
$BV_{CES}$	$I_C = 200$ mA			65			V
$BV_{EBO}$	$I_E = 10$ mA			4.0			V
$I_{CBO}$	$V_{BE} = 30$ V					2.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V	$I_C = 200$ mA		35.0		---	---
$C_{ob}$	$V_{CB} = 28$ V	$f = 1.0$ MHz				250	pF
$f_T$	$V_{CE} = 28$ V	$I_C = 200$ mA	$f = 100$ MHz	50			MHz
$P_G$ $\eta_c$	$V_{CC} = 28$ V	$P_{OUT} = 25$ W		8.5	60		dB %